



**Advanced Power
Electronics Corp.**

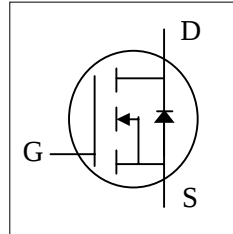
AP4835GMT-HF

Halogen-Free Product

P-CHANNEL ENHANCEMENT MODE

POWER MOSFET

- ▼ Simple Drive Requirement
- ▼ SO-8 Compatible
- ▼ Low On-resistance
- ▼ RoHS Compliant & Halogen-Free

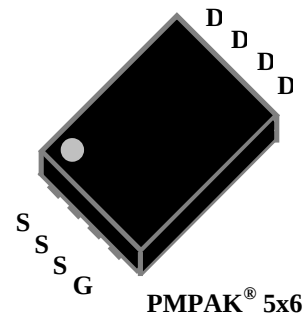


BV_{DSS}	-30V
$R_{DS(ON)}$	21m Ω
I_D	-32A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The PMPAK[®] 5x6 package is special for DC-DC converters application and the foot print is compatible with SO-8 with backside heat sink.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	+25	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current (Chip)	-32	A
$I_D@T_A=25^{\circ}C$	Continuous Drain Current ³	-12.5	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current ³	-10	A
I_{DM}	Pulsed Drain Current ¹	-70	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	31.3	W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation	5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	4	$^{\circ}C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	25	$^{\circ}C/W$



AP4835GMT-HF

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-15A	-	-	21	mΩ
		V _{GS} =-5V, I _D =-10A	-	-	36	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-3	V
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-15A	-	18	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-30V, V _{GS} =0V	-	-	-10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =-15A	-	14	22.4	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-15V	-	3	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	8.5	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =-15V	-	8	-	ns
t _r	Rise Time	I _D =-1A	-	7.5	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	38	-	ns
t _f	Fall Time	V _{GS} =-10V	-	28	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	1175	1880	pF
C _{oss}	Output Capacitance	V _{DS} =-25V	-	195	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	190	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =-15A, V _{GS} =0V	-	-	-1.2	V
t _{rr}	Reverse Recovery Time ²	I _S =-15A, V _{GS} =0V,	-	26	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	16	-	nC

Notes:

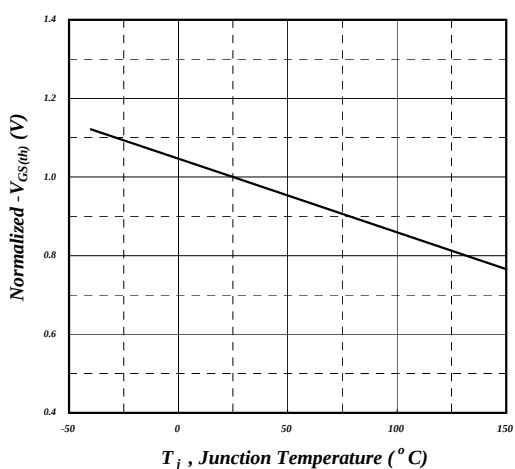
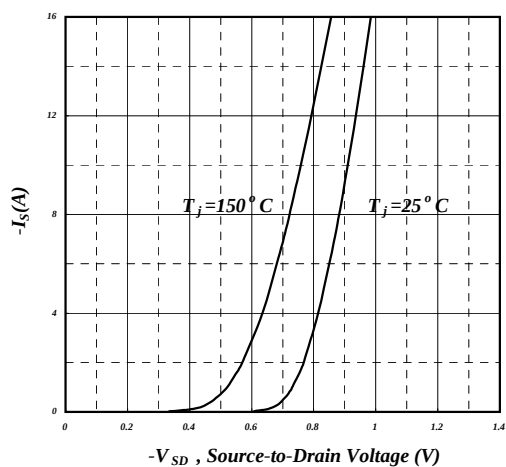
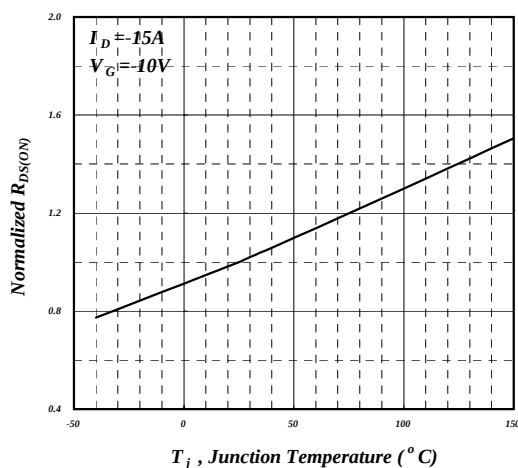
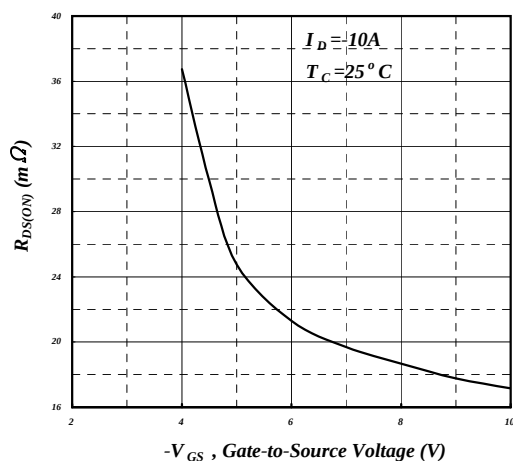
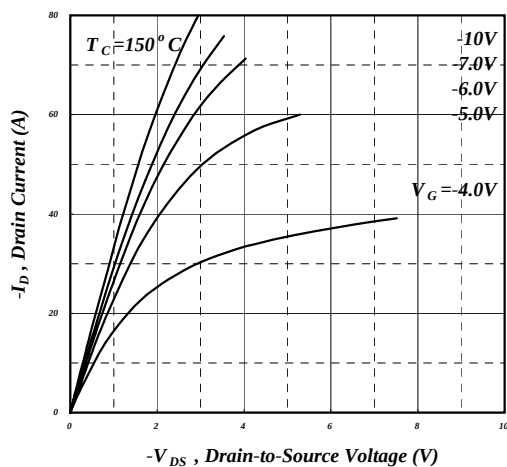
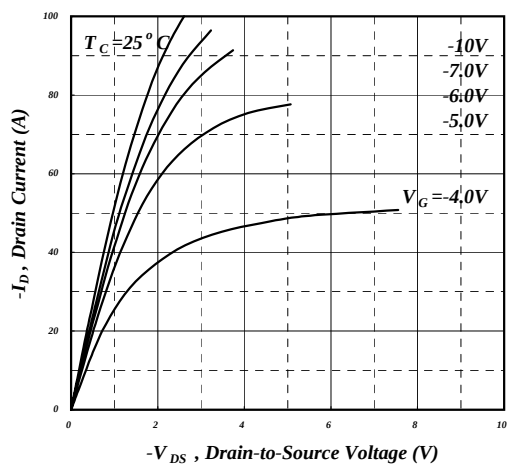
- 1.Pulse width limited by Max. junction temperature
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board, t ≤10sec

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

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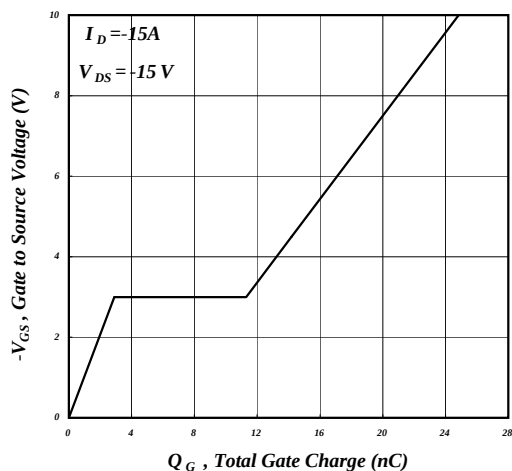


Fig 7. Gate Charge Characteristics

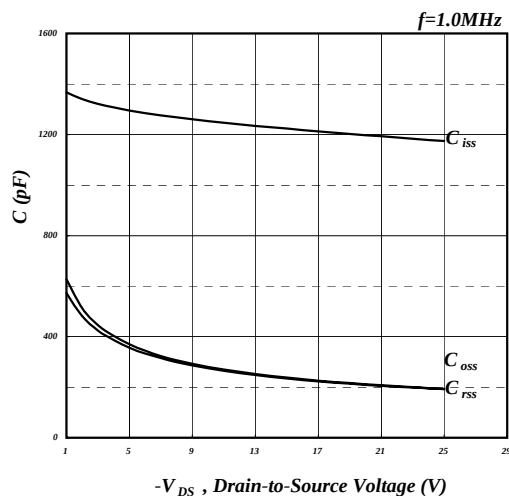


Fig 8. Typical Capacitance Characteristics

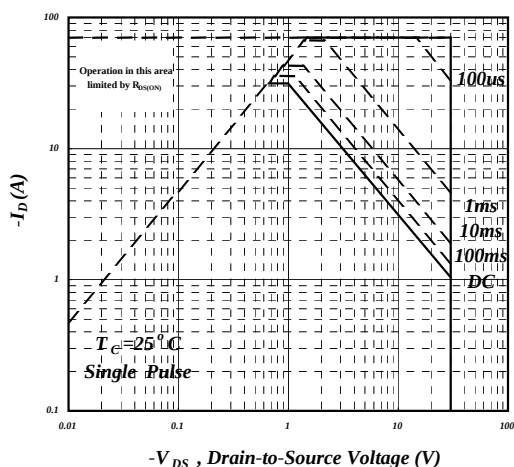


Fig 9. Maximum Safe Operating Area

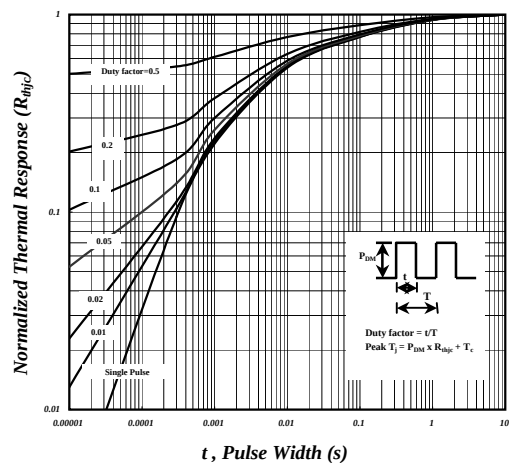


Fig 10. Effective Transient Thermal Impedance

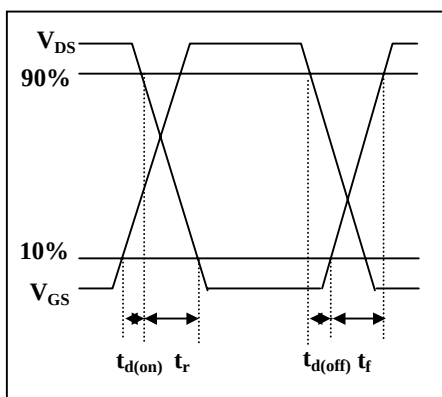


Fig 11. Switching Time Waveform

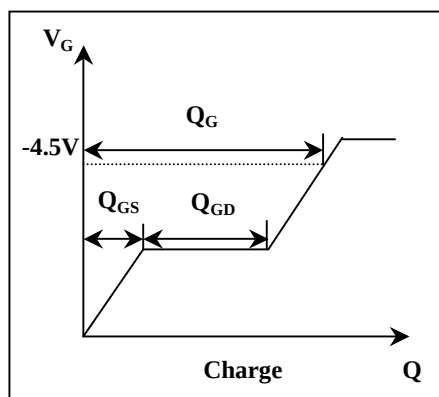


Fig 12. Gate Charge Waveform